

Monolithic Amplifier LHA-13HLN+

500 1MHz to 1 GHz

THE BIG DEAL

- Ultra-High IP3, +43.3 dBm typ.
- Medium power, +28 dBm typ.
- Gain, 22.7 dB typ. at 0.5 GHz
- Excellent Noise Figure, 1.2 dB typ.



Generic photo used for illustration purposes only

CASE STYLE: DQ1225

+RoHS Compliant The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

APPLICATIONS

- Base station infrastructure
- CATV
- Cellular

PRODUCT OVERVIEW

LHA-13HLN+ (RoHS compliant) is an advanced wideband amplifier fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the LHA-13HLN+ has good input and output return loss over a broad frequency range. LHA-13HLN+ is enclosed in a 3mm x 3mm, 12-lead MCLP package and has very good thermal performance.

KEY FEATURES

Feature	Advantages
Broad Band: 1MHz to 1GHz	Broadband covering primary wireless communications bands: VHF, UHF, Cellular
Extremely High IP3 38.1 dBm typical at 1 MHz 43.3 dBm typical at 0.5 GHz	The LHA-13HLN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 12-16 dB above the P1dB point. This feature makes this amplifier ideal for use in: • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra-High Dynamic range receivers
Low Noise Figure 1.2 dB at 0.5 GHz	Enables lower system noise figure performance and along with High OIP3 provides high dynamic range
High P1dB, 28 dBm at 0.5 GHz	High P1dB, High OIP3, Low NF results in a very dynamic range preventing amplifier saturation under strong interfering signals.

REV. A ECO-011665 LHA-13HLN+ MCI NY





Monolithic Amplifier LHA-13HLN+

ELECTRICAL SPECIFICATIONS¹ AT 25°C, 50Ω, UNLESS NOTED OTHERWISE

Parameter	Condition Vd=8V ¹			Units	
Parameter	(MHz)	Min.	Тур.	Max.	Units
requency Range		1		1000	MHz
	1	22.4	24.9	27.4	
	20	_	24.2	_	
Gain	250	_	23.0	_	dB
	500	20.4	22.7	25.0	
	1000	_	20.3	_	
	1		12		
	20		16		
nput Return Loss	250		17		dB
F	500		18		
	1000		12		
	1		12		
	20		18		
Output Return Loss	250		18		dB
	500		30		
	1000		11		
Reverse isolation	500		26		dB
	1		25.7		dBm
	20		26.3		
Output Power @1 dB compression	250		28.1		
	500		28.0		
	1000		26.1		
	1	_	38.1		
	20	_	41.5		
Output IP3 2	250	_	43.6		dBm
·	500	40	43.3		
	1000	_	40.2		
	1		3.0		
	20		1.4		
Noise Figure	250		1.1		dB
•	500		1.2		
	1000		1.4		
Device Operating Voltage			8		V
Device Operating Current			239	251	mA
Device Current Variation vs. Temperature3			-251		μΑ/°C
Device Current Variation vs Voltage			0.0281		mA/mV
Thermal Resistance, junction-to-ground lead			23.3		°C/W

^{1.} Measured on Mini-Circuits Characterization test board TB-1063-13HLN+. See Characterization Test Circuit (Fig. 1)

MAXIMUM RATINGS⁴

Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to 95°C		
Storage Temperature	-65°C to 150°C		
Power Dissipation	3.3 W ⁵		
Input Power (CW)	+21 dBm (5 minutes max) ⁶ +10 dBm (continuous) for 1-10 MHz +11 dBm (continuous) for 10-1000 MHz		
DC Voltage on Pad 7	10V		

^{4.} Permanent damage may occur if any of these limits are exceeded.

^{2.} Tested at Pout= 0 dBm / tone.

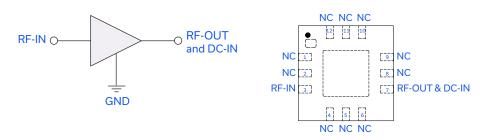
^{3. (}Current at 95° C — Current at -45° C)/140

Electrical maximum ratings are not intended for continuous normal operation.

^{5.} up to 85°C, derate linearly to 2.5 W at 95°C. 6. up to 85°C, derate linearly to 18 dBm at 95°C.

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SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION



Function	Pad Number	Description
RF-IN	3	RF Input
RF-OUT and DC-IN	7	RF Output and DC Bias
GND	Paddle	Connections to ground.
NC	1-2, 4-6, 8-12	No connection, grounded externally

CHARACTERIZATION TEST / RECOMMENDED APPLICATION CIRCUIT

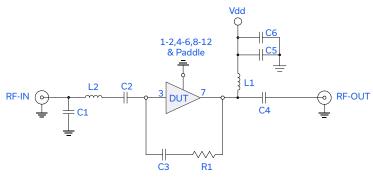


Fig 1. Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-1063-13HLN+)

Gain, Return loss, Output power at 1dB compression (P1 dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Gain and Return loss: Pin= -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/ tone at output.

Components	Size	Value	Manufacturer	P/N
C1	0402	1.5 pF		GRM1555C1H1R5CZ01
C2	0603	2.2 uF	Murata	GRM188R61C225KE15
C3	0402	0.1uF		GRM155R71C104KA88
C4	0603	2.2 uF		GRM188R61C225KE15
C5	0402	1000 pF		GRM1555C1H102JA01
C6	0805	10 uF		GRM21BR61C106KE15
L1	1210	15 uH		LQH32DN150K53L
L2	0603	5.1 nH	Coilcraft	0603CS-5N1XJL
R1	0402	1500 Ω	Koa	RK73H1ET1501F

PRODUCT MARKING



Marking may contain other features or characters for internal lot control



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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASH BOARD. TO ACCESS

CLICK HERE

Performance Data	Data Table Swept Graphs		
Case Style	DQ1225 Plastic package, exposed paddle lead finish: Matte-Tin		
Tape & Reel Standard quantities available on reel	F66 7" reels with 20, 50, 100, 200, 500, 1K, or 2K devices		
Suggested Layout for PCB Design	PL-594		
Evaluation Board	TB-1063-13HLN+		
Environmental Ratings	ENV08T9		

ESD RATING

Human Body Model (HBM): Class 1B (Pass 500 V) in accordance with ANSI/ESD STM 5.1 - 2001

MSL RATING

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020D

MSL FLOW CHART

